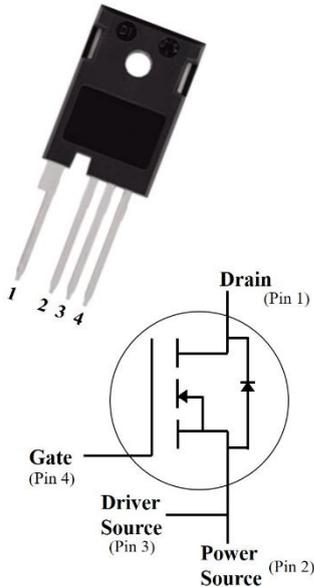


## Silicon Carbide Power MOSFET (N-Channel Enhancement)

$V_{DS}$	750V
$I_D$ (25°C)	82A
$R_{DS(on)}$	25mΩ



### Features

- High speed switching
- Essentially no switching losses
- Reduction of heat sink requirements
- Maximum working temperature at 175 °C
- High blocking voltage
- Fast Intrinsic diode with low recovery current
- High-frequency operation
- Halogen free, RoHS compliant

### Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

### Mechanical Data

- **Package:** TO-247-4L
- **Terminals:** Tin plated leads
- **Polarity:** As marked

### ■ Maximum Ratings ( $T_c=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE	TEST CONDITIONS	NOTE
Device marking code				D207535NCFYG3	
Drain source voltage @ $T_j=25^\circ\text{C}$	$V_{DS,max}$	V	750	$V_{GS}=0V, I_D=100\mu A$	
Gate source voltage @ $T_j=25^\circ\text{C}$	$V_{GS,max}$	V	-8/+22	Absolute maximum values (AC f >1Hz, duty cycle < 1%)	
Gate source voltage @ $T_j=25^\circ\text{C}$	$V_{GS,op}$	V	-5/+18	Recommended operational values	
Continuous drain current @ $T_c=25^\circ\text{C}$	$I_D$	A	82	$V_{GS}=18V, T_c=25^\circ\text{C}$	Fig.17
Continuous drain current @ $T_c=100^\circ\text{C}$			55	$V_{GS}=18V, T_c=100^\circ\text{C}$	
Pulsed drain current	$I_{D(pulsed)}$	A	230	Pulse width $t_p$ limited by $T_{j,max}$	Fig.22
Avalanche energy, Single Pulse	$E_{AS}$	mJ	964	$V_{DD}=75V, L=10mH$	
Power Dissipation	$P_{TOT}$	W	300	$T_c=25^\circ\text{C}, T_j = 175^\circ\text{C}$	Fig.16
Power Dissipation			150	$T_c=100^\circ\text{C}, T_j = 175^\circ\text{C}$	
Operating junction and Storage temperature range	$T_j, T_{stg}$	°C	-55 to +175		
Soldering temperature	$T_L$	°C	260	1.6mm (0.063") from case for 10s	
Mounting torque	$T_M$	Nm	0.6	M3 screw Maximum of mounting process: 3	



# YJD207535NCFYG3

## ■Static Electrical Characteristics (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Gate threshold voltage	$V_{GS(th)}$	V	2.0	3.0	4.0	$V_{DS}=V_{GS}, I_D=12mA$	Fig.4, 11
				2.2		$V_{DS}=V_{GS}, I_D=12mA, T_j=175^\circ C$	
Drain source breakdown voltage	$V_{(BR)DSS}$	V	750			$V_{GS}=0V, I_D=100\mu A$	
Drain source leakage current	$I_{DSS}$	$\mu A$		10	100	$V_{DS}=750V, V_{GS}=0V$	
Gate source leakage current	$I_{GSS}$	nA		10	100	$V_{GS}=18V, V_{DS}=0V$	
Current drain source on-state resistance	$R_{DS(on)}$	m $\Omega$		35		$V_{GS}=15V, I_D=30A$	Fig.5, 6, 7
				25	33	$V_{GS}=18V, I_D=30A$	
				42		$V_{GS}=15V, I_D=30A, T_j=175^\circ C$	
				33		$V_{GS}=18V, I_D=30A, T_j=175^\circ C$	
Transconductance	$g_f$	S		22		$V_{DS}=20V, I_D=30A$	Fig.4
				21		$V_{DS}=20V, I_D=30A, T_j=175^\circ C$	

## ■Dynamic Electrical Characteristics (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Input capacitance	$C_{iss}$	pF		3465		$V_{DS}=500V, V_{GS}=0V, T_j=25^\circ C, f=1MHz, V_{AC}=25mV$	Fig.13, 14
Output capacitance	$C_{oss}$			250			
Reverse capacitance	$C_{rss}$			6			
Coss stored energy	$E_{oss}$	$\mu J$		60.5			Fig.15
Gate source charge	$Q_{gs}$	nC		37		$V_{DS}=500V, V_{GS}=-5/+18V, I_D=30A$	Fig.12
Gate drain charge	$Q_{gd}$			70			
Gate charge	$Q_g$			132			
Internal gate resistance	$R_g$	$\Omega$		1.6		$f=1MHz$	

## ■Switching Characteristics (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Turn on delay time	$t_{d(on)}$	ns		15		$V_{DD}=500V, V_{GS}=-5/+18V, I_D=30A, R_g=2.4\Omega, L=100\mu H$	Fig.21
Rise time	$t_r$			21			
Turn off delay time	$t_{d(off)}$	ns		27			
Fall time	$t_f$			11			



# YJD207535NCFYG3

Turn on switching energy	$E_{on}$	uJ	119	72	$V_{DD}=500V, V_{GS}=-5/+18V, I_D=30A, R_g=2.4\Omega, L=100\mu H$	Fig.19, 20
Turn off switching energy	$E_{off}$					

## ■Body diode characteristics ( $T_c=25^\circ C$ unless otherwise specified )

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Diode forward voltage	$V_{SD}$	V		4.6		$V_{GS}=-5V, I_{SD}=15A$	Fig.8
				2.8		$V_{GS}=0V, I_{SD}=15A, T_j=175^\circ C$	Fig.9
Continuous diode forward current	$I_S$	A		50		$V_{GS}=-5V, T_c=25^\circ C$	
Reverse recovery time	$t_{rr}$	nS		19		$V_R=500V, V_{GS}=-5V, I_D=30A, di/dt=1000A/\mu S$	
Reverse recovery charge	$Q_{rr}$	nC		163			
Peak reverse recovery current	$I_{rrm}$	A		10			

## ■Thermal Characteristics ( $T_a=25^\circ C$ Unless otherwise specified )

PARAMETER	SYMBOL	UNIT	Typ.
Thermal resistance	$R_{\theta J-C}$	$^\circ C/W$	0.5

## ■Typical Characteristics

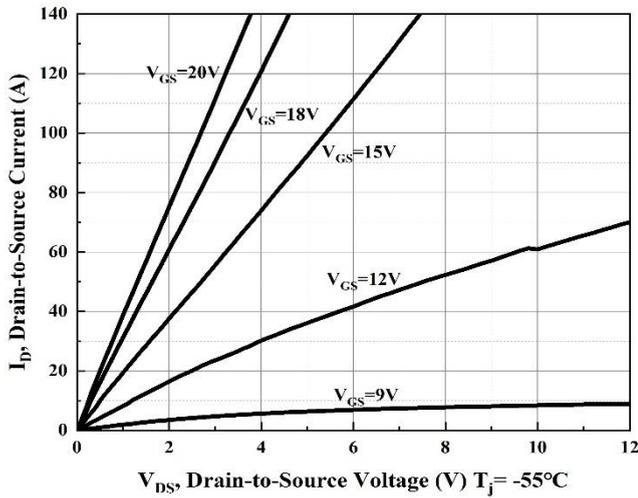


Figure 1. Output Characteristics  $T_j = -55^\circ C$

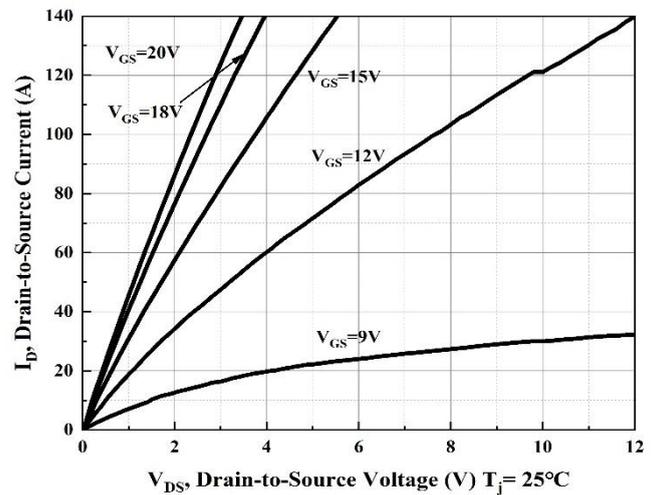


Figure2. Output Characteristics  $T_j = 25^\circ C$



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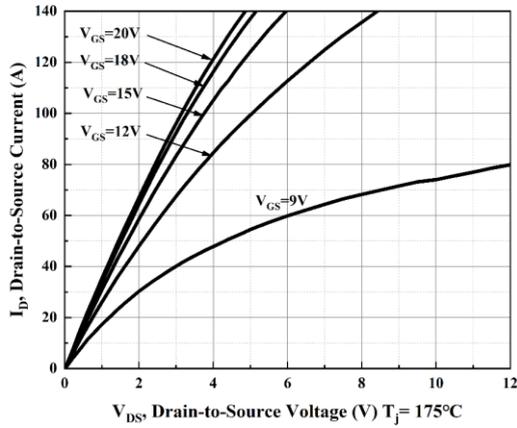


Figure 3. Output Characteristics  $T_j = 175^\circ\text{C}$

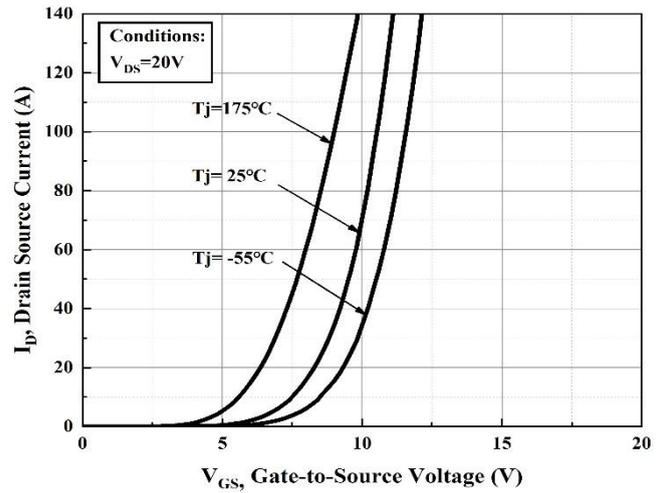


Figure 4. Transfer Characteristics for Various Junction Temperature

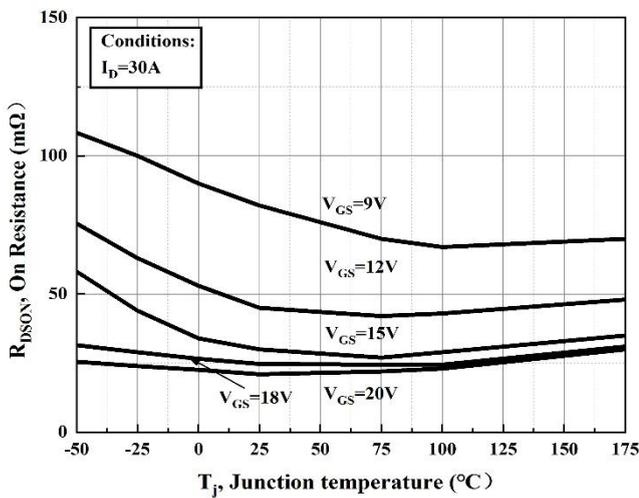


Figure 5. On-resistance vs. Temperature for Various Gate Voltage

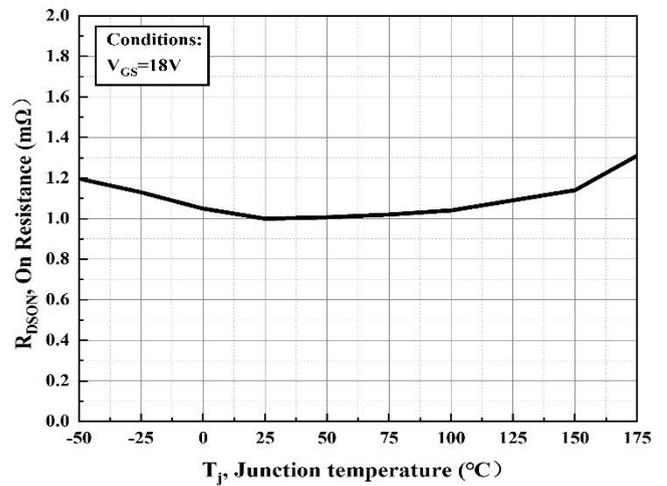


Figure 6. Normalized on-resistance vs. Temperature

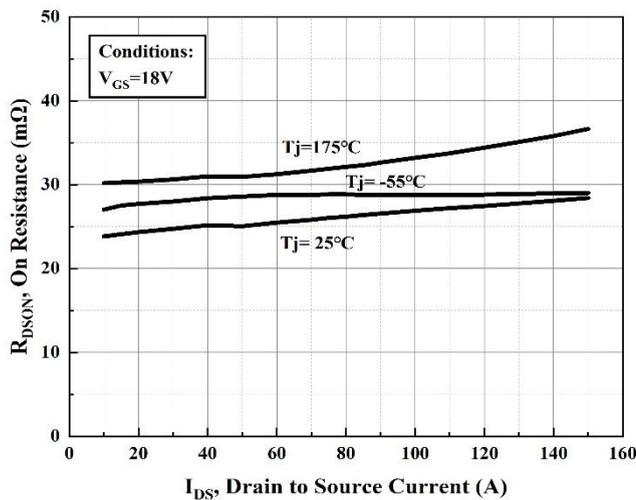


Figure 7. On-resistance vs. Drain Current

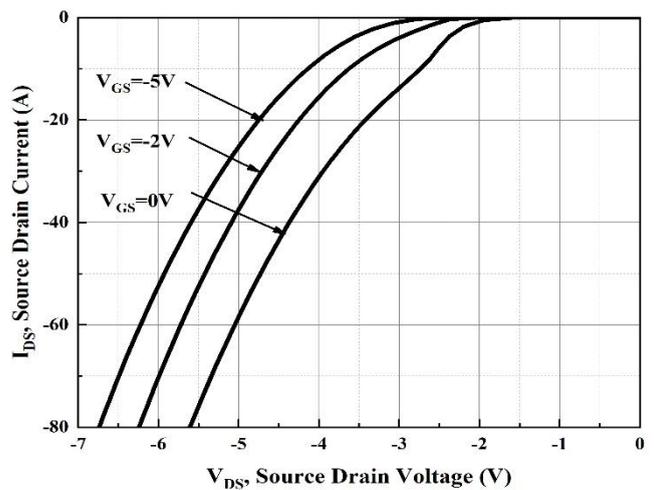


Figure 8. Body Diode Characteristic at  $T_j = 25^\circ\text{C}$



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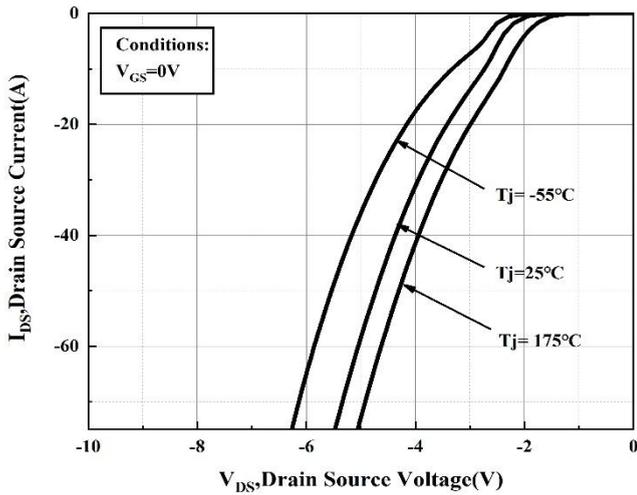


Figure 9. Body Diode Characteristic

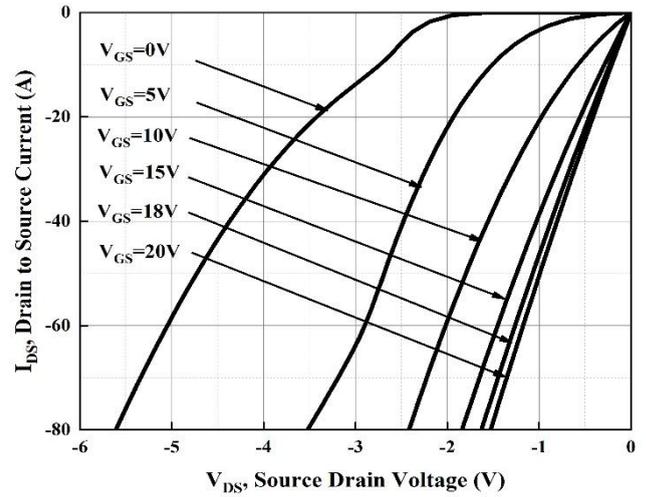


Figure 10. 3<sup>rd</sup> quadrant Characteristic at Tj= 25 °C

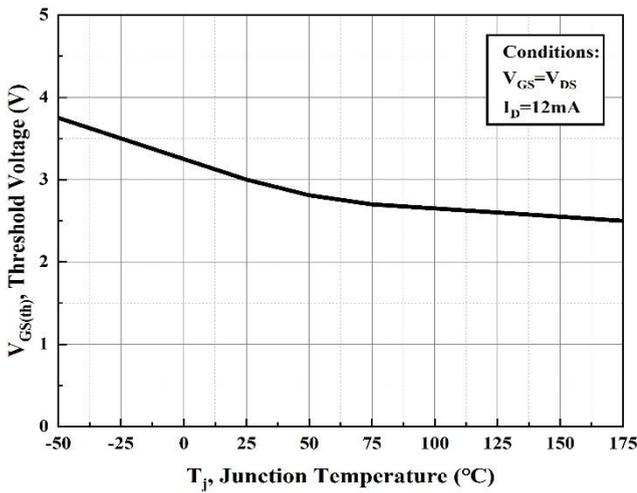


Figure 11. Threshold Voltage vs. Temperature

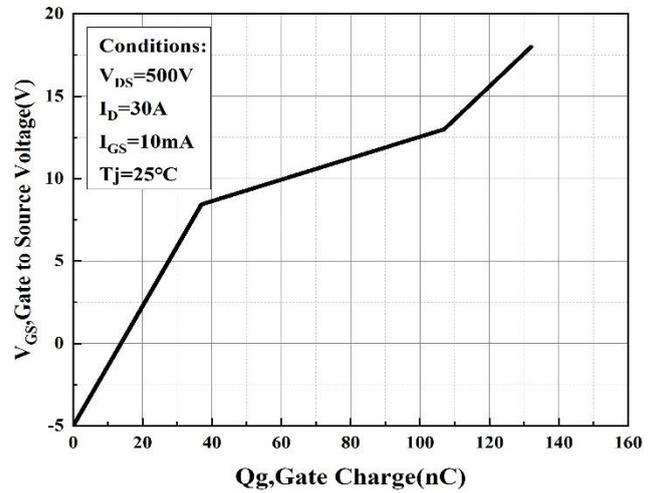


Figure 12. Gate Charge Characteristic

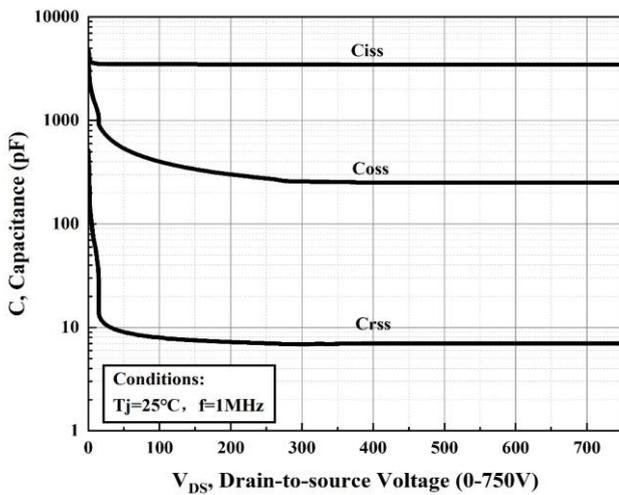


Figure 13. Capacitances vs. Drain Source Voltage (0-750V)

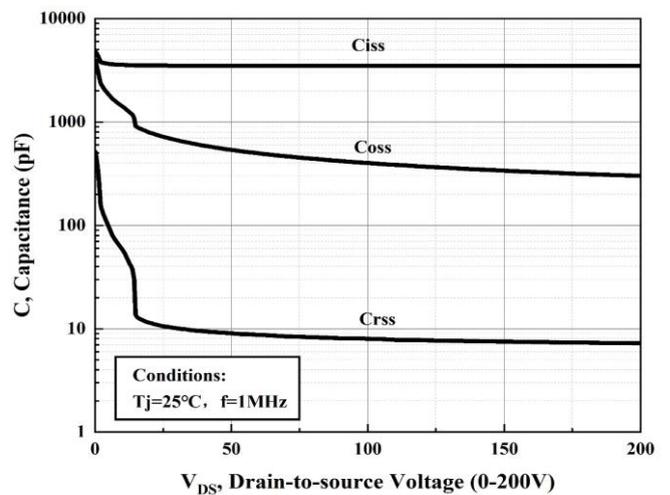


Figure 14. Capacitances vs. Drain Source Voltage (0-200V)



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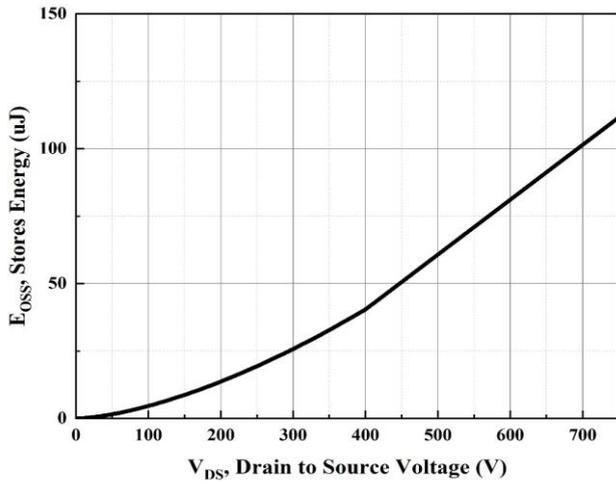


Figure 15. Output Capacitor Stored Energy

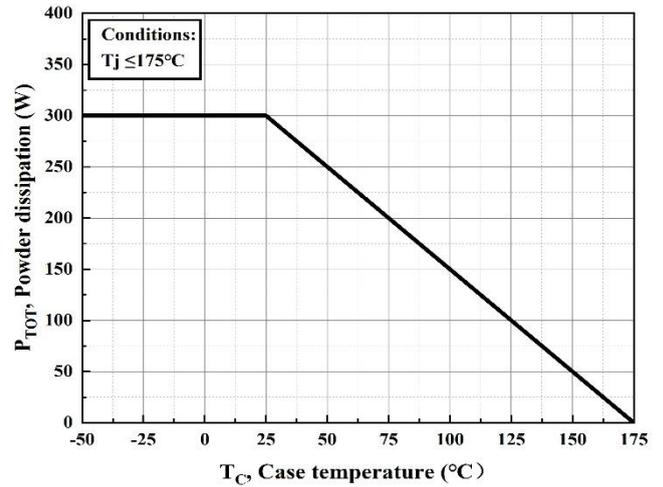


Figure 16. Maximum Power Dissipation Derating vs. Case Temperature

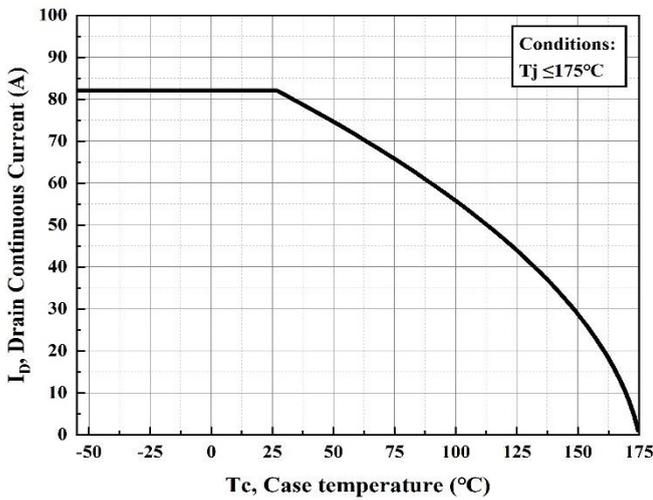


Figure 17. Continuous Drain Current Derating vs. Case Temperature

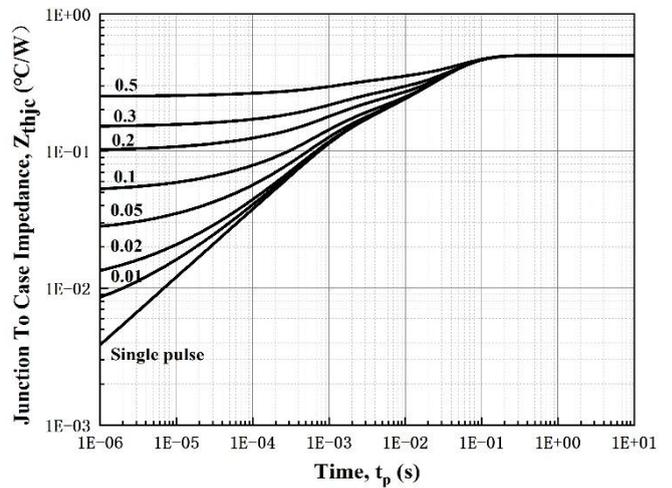


Figure 18. Transient Thermal Impedance (Junction - Case)

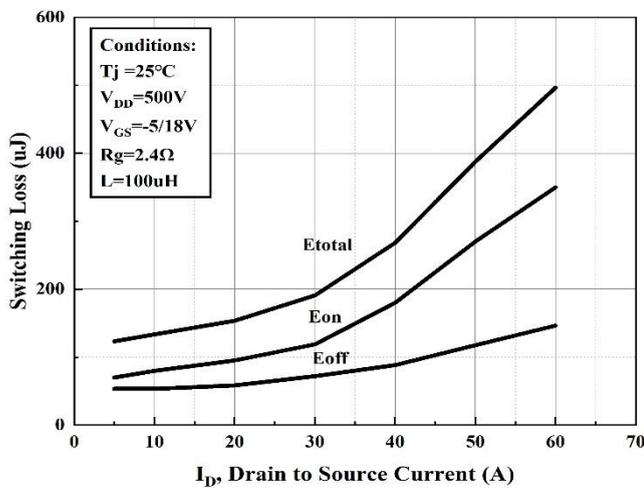


Figure 19. Clamped Inductive Switching Energy vs. Drain Current

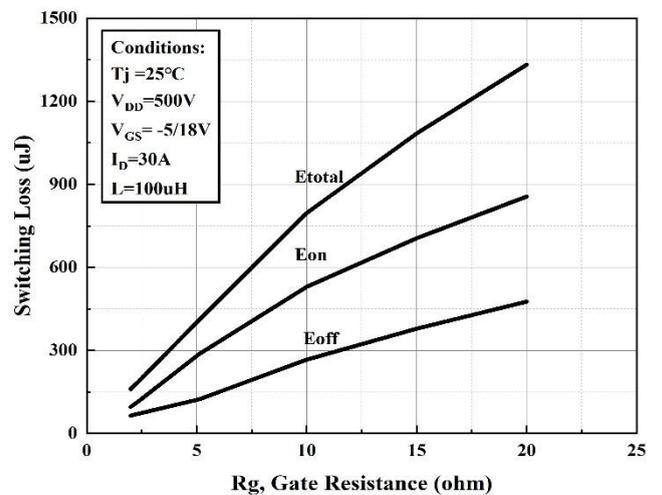


Figure 20. Clamped Inductive Switching Energy vs. R<sub>g</sub>



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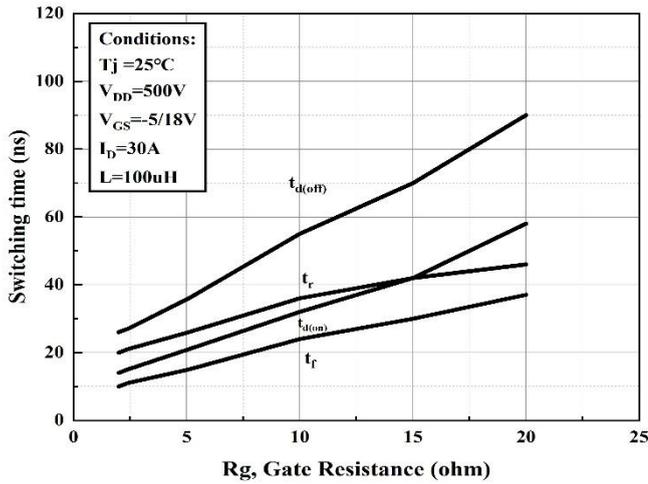


Figure 21. Switching Times vs.  $R_g$

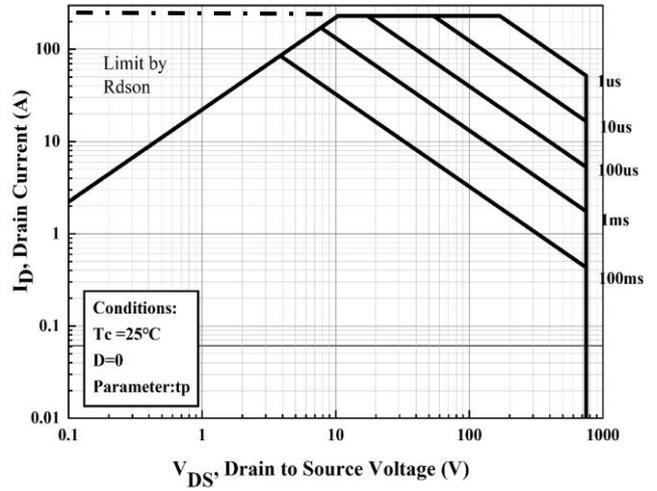


Figure 22. Safe Operating Area

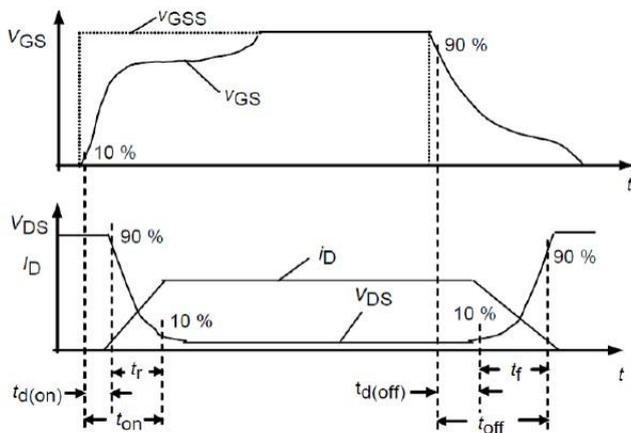


Figure 23. Switching Times Definition

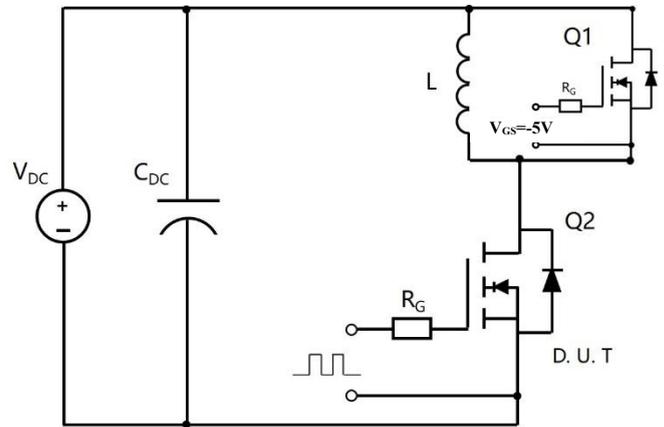
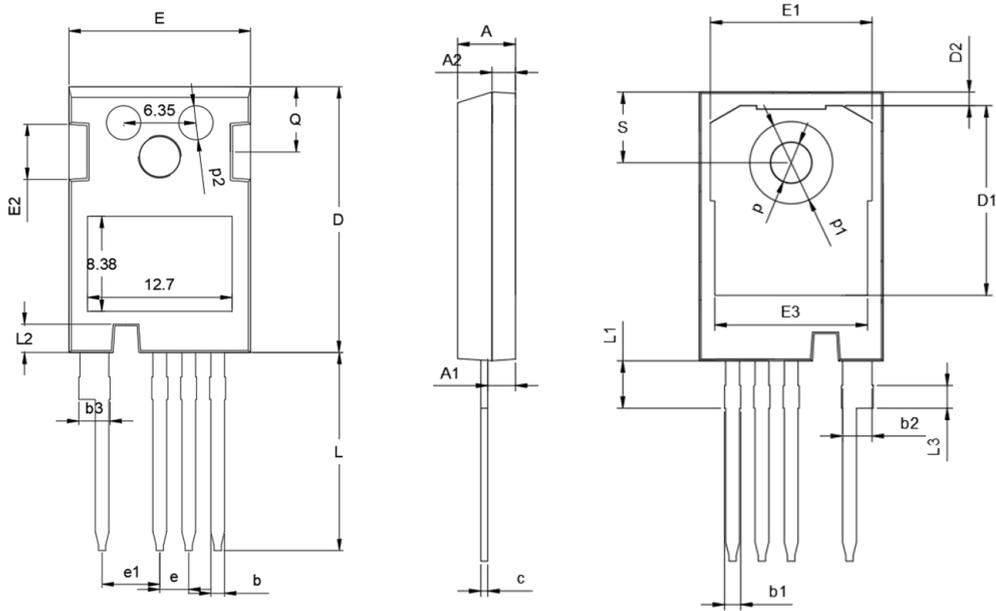


Figure 24. Clamped Inductive Switching Waveform Test Circuit



# YJD207535NCFYG3

## ■Outline Dimensions



TO247-4L			
Dim	Min	Norm	Max
A	4.80	5.00	5.20
A1	2.30	2.40	2.50
A2	1.88	1.98	2.08
b	1.10	1.20	1.30
b1	1.20	/	1.50
b2	2.35	2.55	2.75
b3	2.45	/	2.85
c	0.55	0.60	0.65
D	23.3	23.45	23.6
D1	16.25	16.55	16.85
D2	1.00	/	1.30
e	TYP2.54		
e1	TYP5.06		
E	15.75	15.90	16.05
E1	13.80	/	14.20
E2	4.40	4.75	5.10
E3	13.00	/	13.45
L	17.34	17.49	17.64
L1	4.00	/	4.30
L2	2.35	/	2.65
L3	TYP1.98		
Q	5.60	5.80	6.00
S	6.05	/	6.30
p	TYP3.58		
p1	TYP7.18		
p2	TYP3.00		



## YJD207535NCFYG3

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